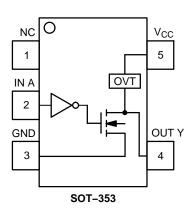
# Single Non-Inverting Buffer with Open Drain Output

The NLV17SZ07 is a high performance single non-inverting buffer with open drain outputs operating from a 1.65 to 5.5 V supply.

The Output stage is open drain with Over Voltage Tolerance. This allows the NLV17SZ07 to be used to interface 5.0 V circuits to circuits of any voltage between 0 and +7.0 V.

#### Features

- Tiny SOT-353 Package
- Extremely High Speed:  $t_{PD}$  2.5 ns (typical) at  $V_{CC}$  = 5 V
- Designed for 1.65 V to 5.5 V  $V_{CC}$  Operation, CMOS Compatible
- Over Voltage Tolerant Inputs  $V_{IN}$  may be Between 0 and 7.0 V for  $V_{CC}$  Between 0.5 and 5.5 V
- TTL Compatible Interface Capability with 5.0 V TTL Logic with  $V_{CC}$  = 2.7 V to 3.6 V
- LVCMOS Compatible
- 24 mA Output Sink Capability, Pullup may be between 0 and 7.0 V
- Near Zero Static Supply Current Substantially Reduces System Power Requirements
- Chip Complexity: FET = 20
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q100 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant



#### Figure 1. Pinout

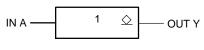
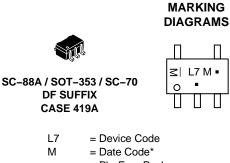


Figure 2. Logic Symbol



# **ON Semiconductor®**

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= Pb–Free Package

(Note: Microdot may be in either location) \*Date Code orientation and/or position may vary depending upon manufacturing location.

#### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

#### **PIN ASSIGNMENT**

Pin	Function
1	NC
2	IN A
3	GND
4	OUT Y
5	V <sub>CC</sub>

#### **FUNCTION TABLE**

Input	Output
A	Y
L	L
н	Z

#### **MAXIMUM RATINGS**

Symbol		Value	Unit	
V <sub>CC</sub>	DC Supply Voltage		-0.5 to +7.0	V
VI	DC Input Voltage		$-0.5 \le V_1 \le +7.0$	V
V <sub>O</sub>	DC Output Voltage	Active Mode, LOW State (Note 1) Tri–State Mode Power–Down Mode (V <sub>CC</sub> = 0 V)	-0.5 to V <sub>CC</sub> + 0.5 -0.5 to +7.0 -0.5 to +7.0	V
I <sub>OK</sub>	DC Output Diode Current	V <sub>O</sub> < GND	-50	mA
Ι <sub>ΙΚ</sub>	DC Input Diode Current	V <sub>I</sub> < GND	-50	mA
Ι <sub>Ο</sub>	DC Output Sink Current		±50	mA
I <sub>CC</sub>	DC Supply Current per Supply	Pin	±100	mA
I <sub>GND</sub>	DC Ground Current per Ground	±100	mA	
T <sub>STG</sub>	Storage Temperature Range		-65 to +150	°C
PD	Power Dissipation in Still Air		186	mW
$\theta_{JA}$	Thermal Resistance		350	°C/W
ΤL	Lead Temperature, 1 mm from	Case for 10 Seconds	260	°C
TJ	Junction Temperature Under Bi	as	+150	°C
I <sub>Latch-Up</sub>	Latch–Up Performance	Above $V_{CC}$ and Below GND at 85°C (Note 5)	±500	mA
MSL	Moisture Sensitivity		Level 1	
F <sub>R</sub>	Flammability Rating	Oxygen Index: 28 to 34	UL 94 V–0 @ 0.125 in	
ESD	ESD Classification	Human Body Model (Note 3) Machine Model (Note 4) Charged Device Model (Note 5)	Class 2 Class B N/A	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.
I<sub>O</sub> absolute maximum rating must be observed.
Tested to EIA/JESD22-A114-A, rated to EIA/JESD22-A114-B.
Tested to EIA/JESD22-A115-A, rated to EIA/JESD22-A115-A.

Tested to JESD22–C101–A.
 Tested to EIA/JESD78.

#### **RECOMMENDED OPERATING CONDITIONS**

Symbol	Parar	Min	Max	Unit	
V <sub>CC</sub>	Supply Voltage	Operating Data Retention Only	1.65 1.5	5.5 5.5	V
VI	Input Voltage		0	5.5	V
V <sub>O</sub>	Output Voltage	Active Mode, LOW State Tri–State Mode Power–Down Mode (V <sub>CC</sub> = 0 V)	0 0 0	V <sub>CC</sub> 5.5 5.5	V
T <sub>A</sub>	Operating Free–Air Temperature		-55	+125	°C
Δt/ΔV	Input Transition Rise or Fall Rate	$\begin{array}{l} V_{CC} = 2.5 \ V \pm 0.2 \ V \\ V_{CC} = 3.0 \ V \pm 0.3 \ V \\ V_{CC} = 5.0 \ V \pm 0.5 \ V \end{array}$	0 0 0	20 10 5	ns/V

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

#### DC ELECTRICAL CHARACTERISTICS

		Condition	v	Т	T <sub>A</sub> = 25°C			$-55^\circ C \leq T_A \leq 125^\circ C$	
Symbol Parameter	Parameter		V <sub>CC</sub> (V)	Min	Тур	Max	Min	Max	Unit
V <sub>IH</sub>	High–Level Input Voltage		1.65 to 1.95 2.3 to 5.5	0.75 V <sub>CC</sub> 0.7 V <sub>CC</sub>			0.75 V <sub>CC</sub> 0.7 V <sub>CC</sub>		V
V <sub>IL</sub>	Low–Level Input Voltage		1.65 to 1.95 2.3 to 5.5			0.25 V <sub>CC</sub> 0.3 V <sub>CC</sub>		0.25 V <sub>CC</sub> 0.3 V <sub>CC</sub>	V
I <sub>LKG</sub>	Z–State Output Leakage Current	V <sub>IN</sub> = V <sub>IH</sub> V <sub>OUT</sub> = V <sub>CC</sub> or GND	2.3 to 5.5			±5.0		±10.0	μΑ
V <sub>OL</sub>	Low-Level Output	I <sub>OL</sub> = 100 μA	1.65 to 5.5		0.0	0.1		0.1	V
	Voltage V <sub>IN</sub> = V <sub>IL</sub>	$I_{OL} = 4 \text{ mA}$	1.65		0.08	0.24		0.24	
		I <sub>OL</sub> = 8 mA	2.3		0.20	0.3		0.3	
		I <sub>OL</sub> = 12 mA	2.7		0.22	0.4		0.4	
		I <sub>OL</sub> = 16 mA	3.0		0.28	0.4		0.4	
		I <sub>OL</sub> = 24 mA	3.0		0.38	0.55		0.55	
		I <sub>OL</sub> = 32 mA	4.5		0.42	0.55		0.55	
I <sub>IN</sub>	Input Leakage Current	$V_{IN}$ = 5.5 V or GND	0 to 5.5			±0.1		±1.0	μΑ
I <sub>OFF</sub>	Power Off Leakage Current	V <sub>IN</sub> = 5.5 V or V <sub>OUT</sub> = 5.5 V	0			1		10	μΑ
I <sub>CC</sub>	Quiescent Supply Current	$V_{IN} = 5.5 \text{ V or GND}$	5.5			1		10	μΑ
I <sub>CCT</sub>	Quiescent Supply Current	V <sub>IN</sub> = 3.0 V	3.6			10		100	μΑ

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

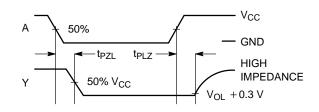
			$T_{A} = 25^{\circ}C \qquad -55^{\circ}C \le T_{A} \le 125^{\circ}C$		T <sub>A</sub> = 25°C		<sub>A</sub> ≤ 125°C		
Symbol	Parameter	Condition	V <sub>CC</sub> (V)	Min	Тур	Max	Min	Max	Unit
t <sub>PZL</sub>	t <sub>PZL</sub> Propagation Delay $R_{L} = R_1 = 500 \Omega, C_L = 50 pF$ (Figure 3 and 4)		$1.8\pm0.15$	0.8	5.3	11.6	0.8	12.0	ns
		$2.5\pm0.2$	1.2	3.7	5.8	1.2	6.4		
			$3.3\pm0.3$	0.8	2.9	4.4	0.8	4.8	
			$5.0\pm0.5$	0.5	2.3	3.5	0.5	3.9	
t <sub>PLZ</sub>	t <sub>PLZ</sub> Propagation Delay (Figure 3 and 4)		$1.8\pm0.15$	0.8	5.3	11.6	0.8	1.20	ns
		)	$2.5\pm0.2$	1.2	2.8	5.8	1.2	6.4	
			$3.3\pm0.3$	0.8	2.1	4.4	0.8	4.8	
			$5.0\pm0.5$	0.5	1.4	3.5	0.5	3.9	

#### AC ELECTRICAL CHARACTERISTICS $t_R$ = $t_F$ = 2.5 ns; $C_L$ = 50 pF; $R_L$ = 500 $\Omega$

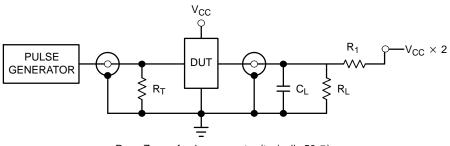
#### **CAPACITIVE CHARACTERISTICS**

Symbol	Parameter	Condition	Typical	Unit
C <sub>IN</sub>	Input Capacitance	$V_{CC}$ = 5.5 V, $V_{I}$ = 0 V or $V_{CC}$	>2.5	pF
C <sub>OUT</sub>	Output Capacitance	$V_{CC}$ = 5.5 V, $V_{I}$ = 0 V or $V_{CC}$	4.0	pF
C <sub>PD</sub>	Power Dissipation Capacitance (Note 6)	10 MHz, $V_{CC}$ = 5.5 V, $V_{I}$ = 0 V or $V_{CC}$	4.0	pF

6.  $C_{PD}$  is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation:  $I_{CC(OPR)} = C_{PD} \bullet V_{CC} \bullet f_{in} + I_{CC}$ .  $C_{PD}$  is used to determine the no–load dynamic power consumption;  $P_D = C_{PD} \bullet V_{CC} \bullet f_{in} + I_{CC} \bullet V_{CC}$ .







 $R_T = Z_{OUT}$  of pulse generator (typically 50  $\Omega$ )

Figure 4. Test Circuit

#### **DEVICE ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>		
NLV17SZ07DFT2G*	SOT-353/SC70-5/SC-88A (Pb-Free)	3000 / Tape & Reel		

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
 \*NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q100 Qualified and PPAP

Capable.





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